


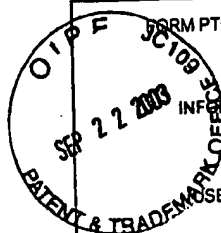
 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (SEE SEVERAL SHEETS IF NECESSARY)	U.S. PAT. NO. 5,014,149 ATTY. DOCKET NO. ASMEEX.284DV1	APPLICATION NO. 10/628,217
	APPLICANT Pomarado, et al.	
	FILING DATE July 24, 2003	GROUP Unknown

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
CX	1	2,394,930	2/12/46	McRae			
CX	2	3,895,127	7/15/75	Comizzoli			
CX	3	4,056,642	11/1/77	Saxena et al.			
CX	4	4,292,343	9/29/81	Plaettner et al.			
CX	5	4,343,830	8/10/82	Sarma et al.			
CX	6	4,436,761	3/13/84	Hayashi et al.			
CX	7	4,544,571	10/1/85	Miller			
CX	8	4,645,683	2/24/87	Gourier et al.			
CX	9	4,766,006	8/23/88	Gaczi			
CX	10	5,135,775	8/4/92	Foller et al.			
CX	11	5,281,546	01/25/94	Possin et al.			
CX	12	5,576,071	11/19/96	Sandhu			
CX	13	5,587,205	12/24/96	Saito et al.			
CX	14	5,780,115	7/14/98	Park et al.			
CX	15	5,939,763	08/17/99	Hao et al.			
CX	16	5,950,107	09/07/99	Huff et al.			
CX	17	5,990,013	11/23/99	Berenguer et al.			
CX	18	5,993,916	11/30/99	Zhao et al.			
CX	19	6,107,192	08/22/00	Subrahmanyam et al.			
CX	20	6,200,866	03/13/01	Ma et al.			

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	21	JP 60 254621 A	16.12.85	Patent Abstracts of Japan				
	22	JP 2000 160342 A	13.10.00	Patent Abstracts of Japan				
	23	0 617 461 A2	03/16/94	EPO				

EXAMINER <i>Christy Karasick</i>	DATE CONSIDERED <i>6/26/04</i>
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	



FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
ASMEX.284DV1APPLICATION NO.  
10/626,217INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT  
Pomarede, et al.FILING DATE  
July 24, 2003GROUP  
Unknown

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
<i>JS</i>	24 Kim, H. and R. Reif, <i>Thin Solid Films</i> , Vol. 289:192-198 (1996), "In-situ low-temperature (600°C) wafer surface cleaning by electron cyclotron resonance hydrogen plasma ...."
<i>JS</i>	25 Ramm J. and E. Beck, <i>Thin Solid Films</i> , Vol. 246:158-163 (1994), "Low temperature epitaxial growth by molecular beam epitaxy on hydrogen-plasma-cleaned silicon wafers."

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EXAMINER <i>Christy Kerslake</i>	DATE CONSIDERED <i>6/26/04</i>
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